

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

OptiMOS™ Power-Transistor, 80V

OptiMOS™3 Power-Transistor
IPA057N08N3 G

Data Sheet

Rev. 2.2
Final

OptiMOS™³ Power-Transistor
Features

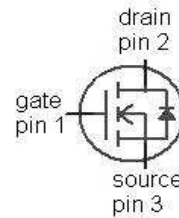
- Ideal for high frequency switching and sync. rec.
- Optimized technology for DC/DC converters
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Halogen-free according to IEC61249-2-21
- Fully isolated package (2500 VAC; 1 minute)

Product Summary

V_{DS}	80	V
$R_{DS(on),max}$	5.7	m Ω
I_D	60	A



Type	IPA057N08N3 G
Package	PG-TO220-FP
Marking	057N08N


Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25\text{ °C}^2)$	60	A
		$T_C=100\text{ °C}$	43	
Pulsed drain current ³⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	240	
Avalanche energy, single pulse ⁴⁾	E_{AS}	$I_D=60\text{ A}, R_{GS}=25\ \Omega$	290	mJ
Gate source voltage	V_{GS}		± 20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	39	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

¹⁾J-STD20 and JESD22

²⁾ Current is limited by package; with an $R_{thJC}=1\text{ K/W}$ in a standard TO-220 package the chip is able to carry 119A.

³⁾ See figure 3 for more detailed information

⁴⁾ See figure 13 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	3.8	K/W
-------------------------------------	------------	--	---	---	-----	-----

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	80	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=90\text{ }\mu\text{A}$	2	2.8	3.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=60\text{ A}$	-	4.9	5.7	m Ω
		$V_{GS}=6\text{ V}, I_D=30\text{ A}$	-	6.3	9.9	
Gate resistance	R_G		-	2.2	-	Ω
Transconductance	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=60\text{ A}$	45	90	-	S

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=40\text{ V},$ $f=1\text{ MHz}$	-	3570	4750	pF
Output capacitance	C_{oss}		-	963	1280	
Reverse transfer capacitance	C_{rss}		-	36	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=40\text{ V}, V_{GS}=10\text{ V},$ $I_D=60\text{ A}, R_{G,ext}=1.6\ \Omega$	-	17	-	ns
Rise time	t_r		-	42	-	
Turn-off delay time	$t_{d(off)}$		-	36	-	
Fall time	t_f		-	9	-	

Gate Charge Characteristics⁵⁾

Gate to source charge	Q_{gs}	$V_{DD}=40\text{ V}, I_D=60\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	18	-	nC
Gate to drain charge	Q_{gd}		-	10	-	
Switching charge	Q_{sw}		-	18	-	
Gate charge total	Q_g		-	52	69	
Gate plateau voltage	$V_{plateau}$		-	5.0	-	V
Output charge	Q_{oss}	$V_{DD}=40\text{ V}, V_{GS}=0\text{ V}$	-	70	93	nC

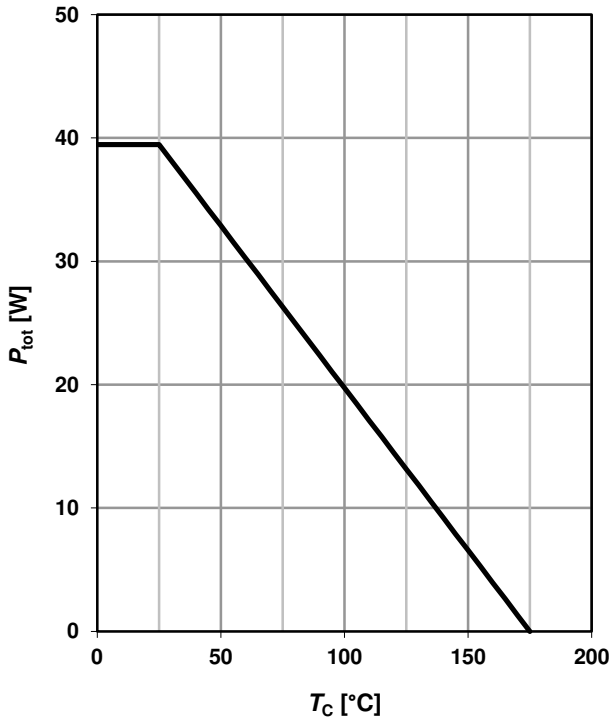
Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ °C}$	-	-	60	A
Diode pulse current	$I_{S,pulse}$		-	-	240	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=60\text{ A},$ $T_j=25\text{ °C}$	-	1.0	1.2	V
Reverse recovery time	t_{rr}	$V_R=40\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	64	-	ns
Reverse recovery charge	Q_{rr}		-	121	-	nC

⁵⁾ See figure 16 for gate charge parameter definition

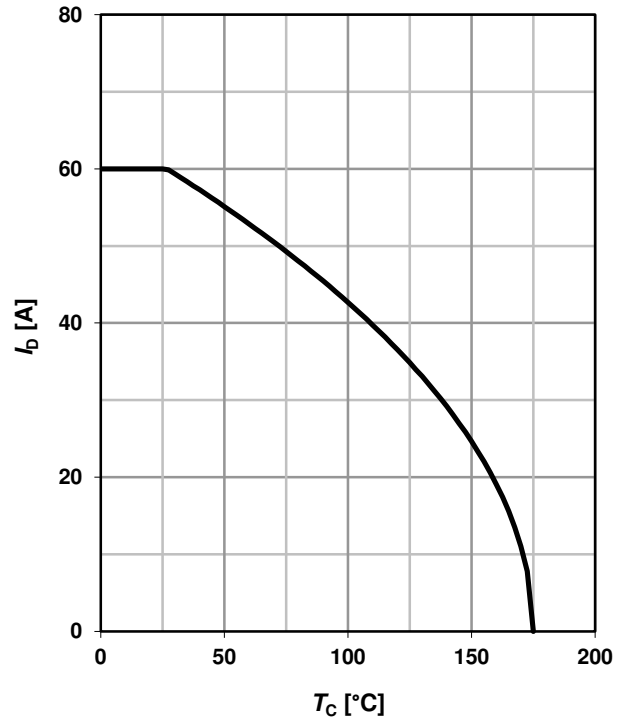
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

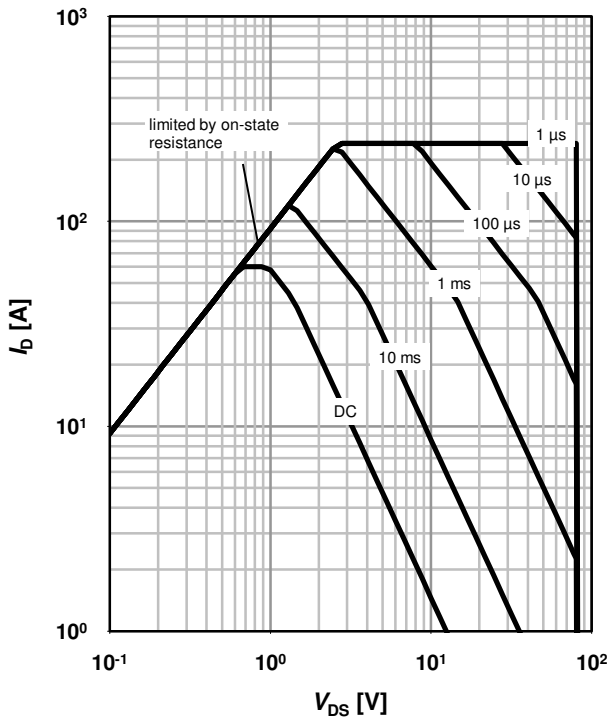
$I_D=f(T_C); V_{GS} \geq 10\text{ V}$



3 Safe operating area

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

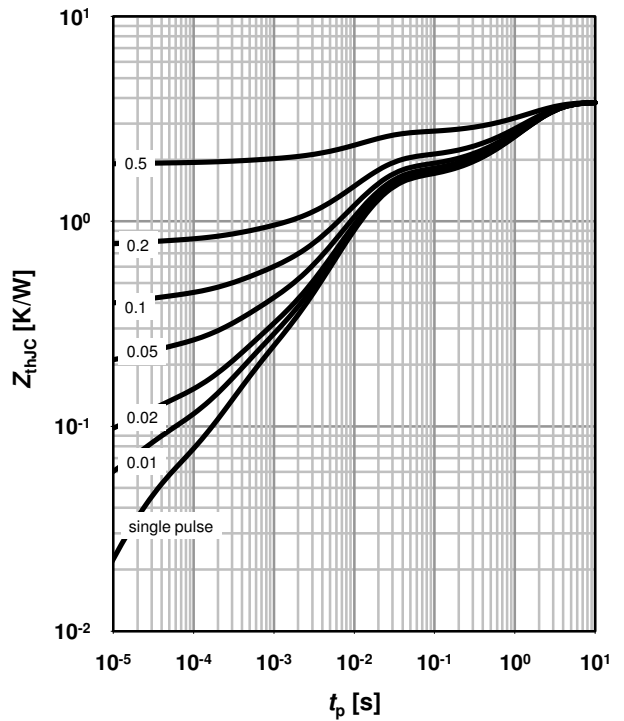
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

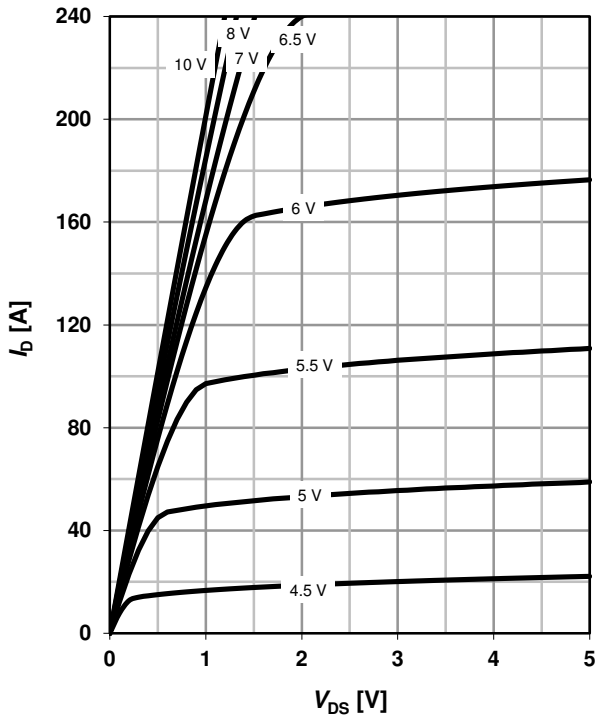
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

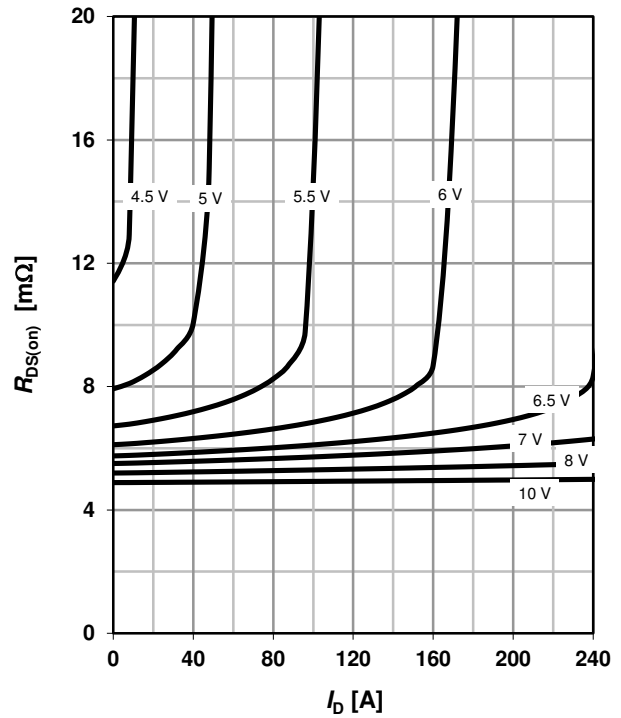
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

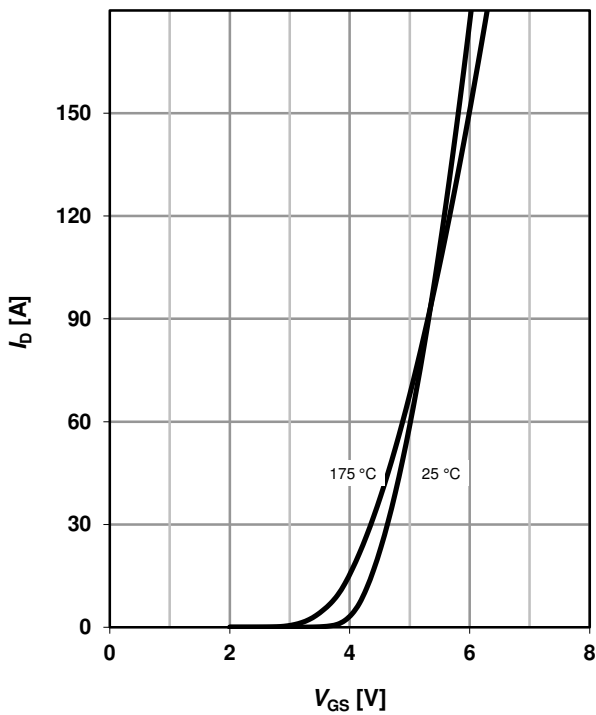
parameter: V_{GS}



7 Typ. transfer characteristics

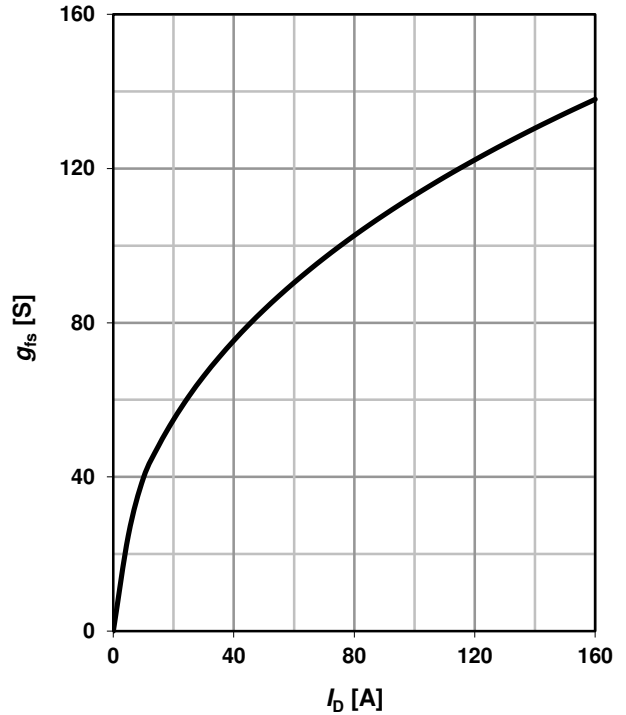
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_j



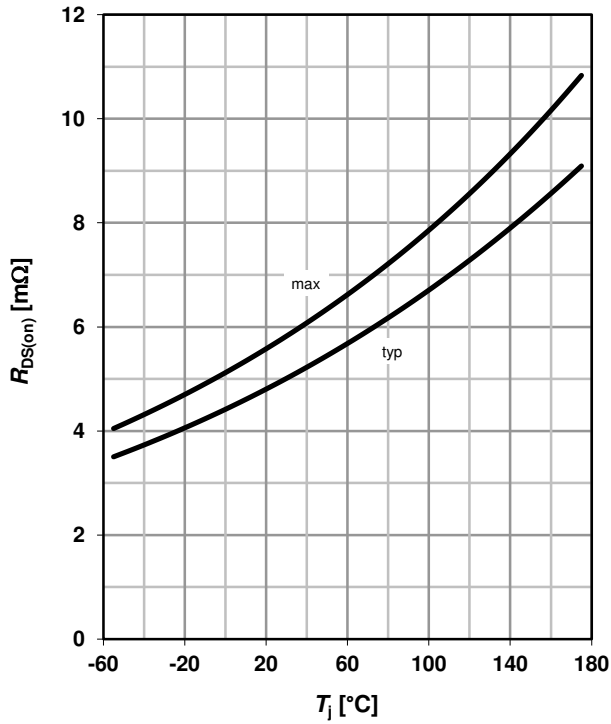
8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



9 Drain-source on-state resistance

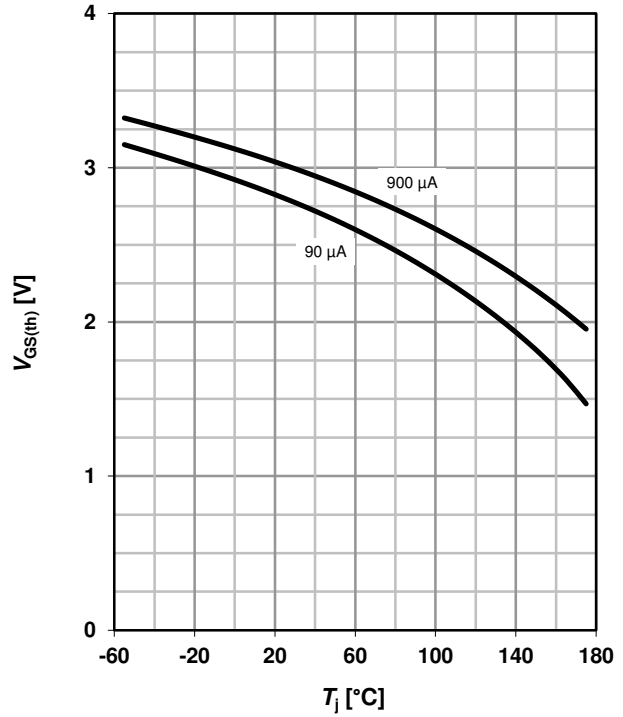
$R_{DS(on)}=f(T_j); I_D=60\text{ A}; V_{GS}=10\text{ V}$



10 Typ. gate threshold voltage

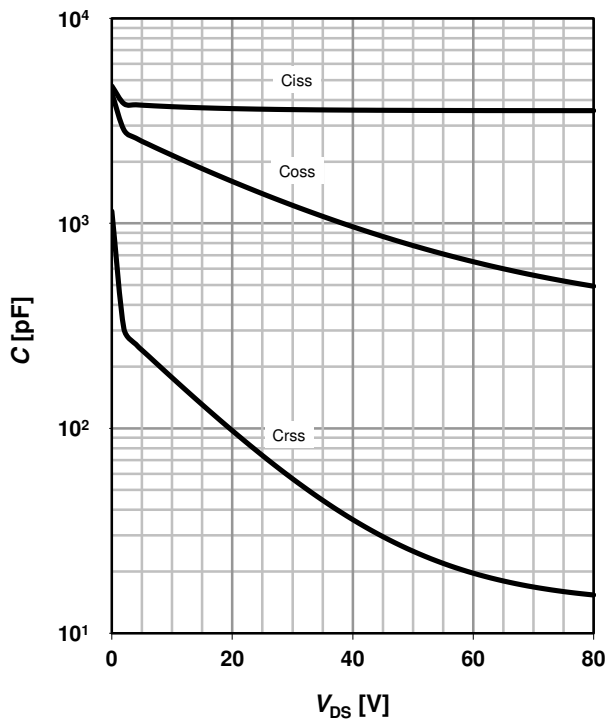
$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}$

parameter: I_D



11 Typ. capacitances

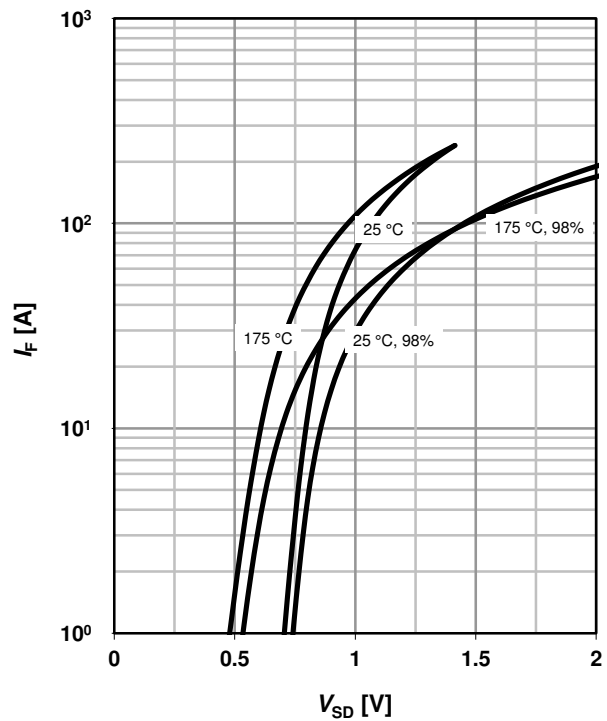
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



12 Forward characteristics of reverse diode

$I_F=f(V_{SD})$

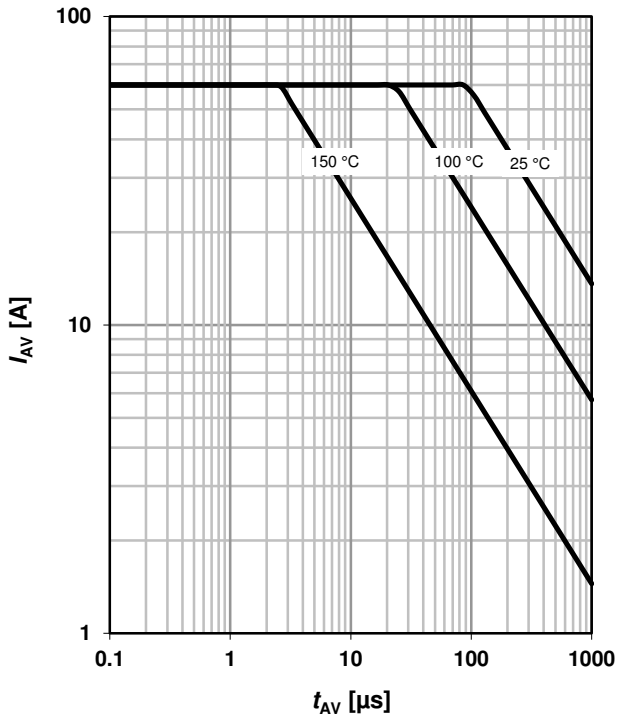
parameter: T_j



13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

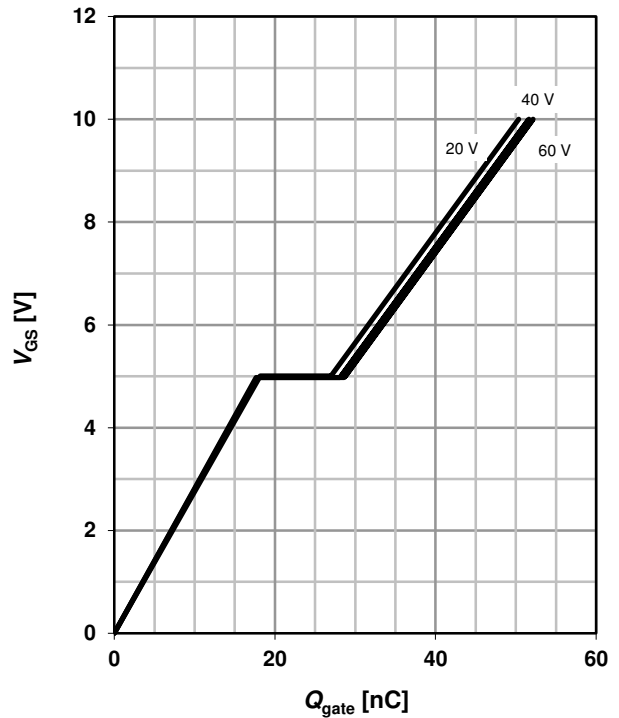
parameter: $T_{j(\text{start})}$



14 Typ. gate charge

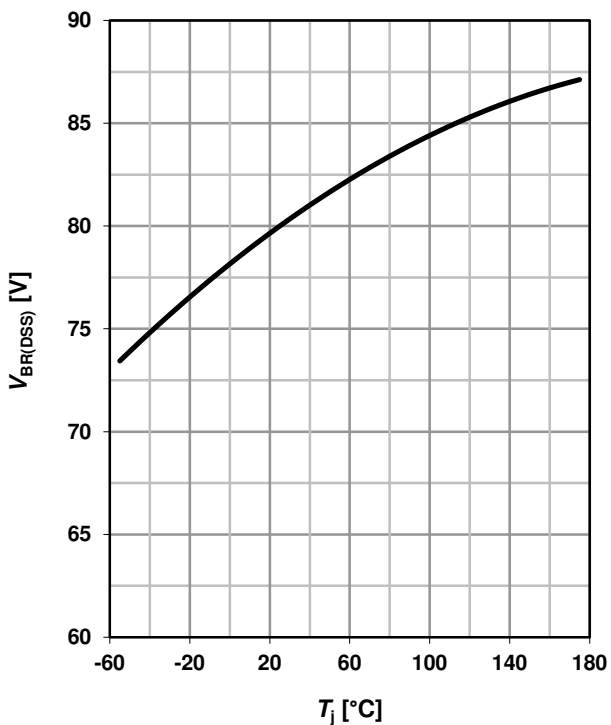
$V_{GS}=f(Q_{\text{gate}}); I_D=60 \text{ A pulsed}$

parameter: V_{DD}

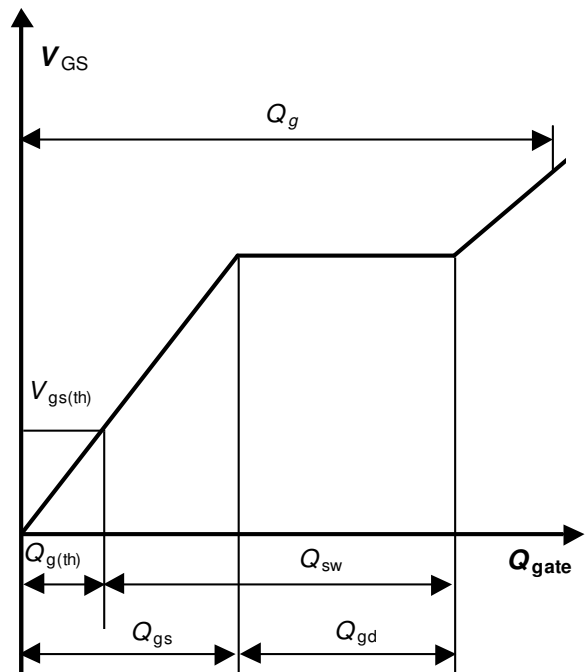


15 Drain-source breakdown voltage

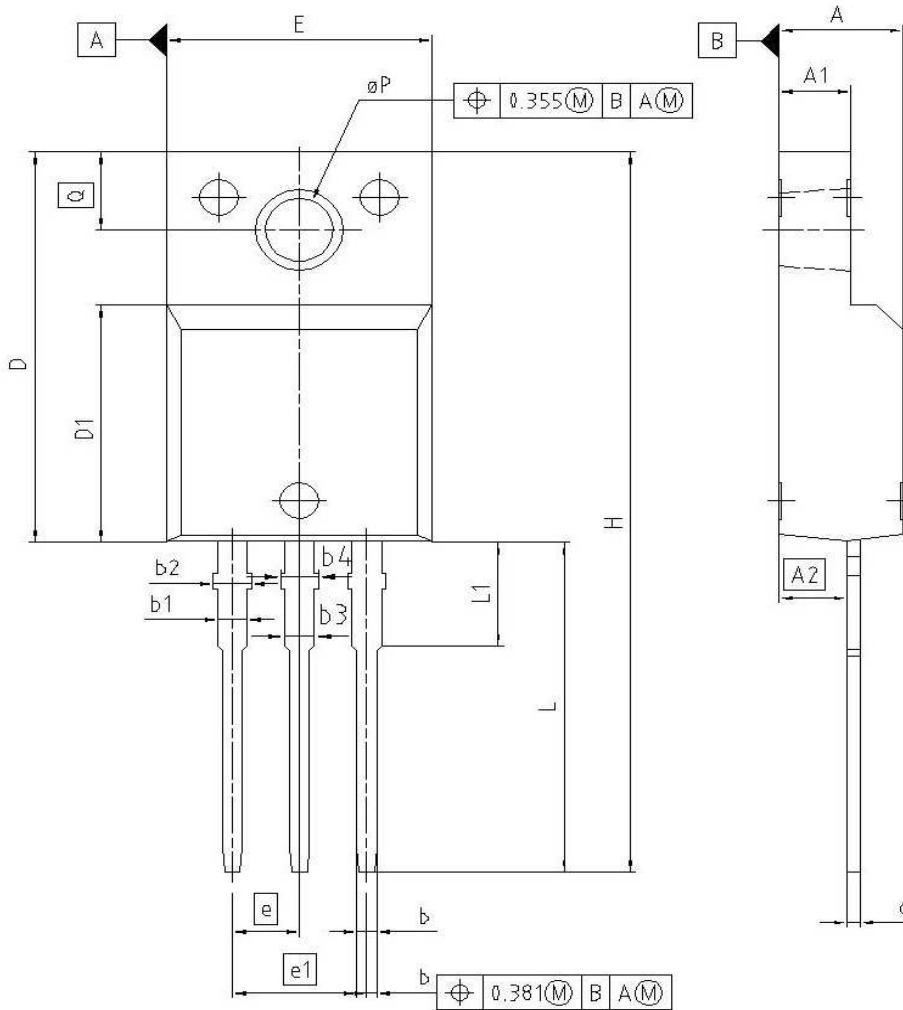
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



16 Gate charge waveforms



PG-TO-220-3-31



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
$\varnothing P$	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

REFERENCE
..

SCALE
0 2.5 5mm

EUROPEAN PROJECTION

ISSUE DATE
08-01-2007

FILE
TO220_2

Revision History

IPA057N08N3 G

Revision: 2015-08-27, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.2	2015-08-27	Update features: "Fully isolated package..."

We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

erratum@infineon.com

Published by

Infineon Technologies AG

81726 München, Germany

© 2015 Infineon Technologies AG

All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.